

**VSP-MIKRON** $V_{RRM}=1800V$  $I_F = 100A$ **Diode-Die****KD100180F**

Die Size-10.8 x 8.3mm.

Ultra low losses

Passivation : Silicon Oxide plus Polyimide

Maximum rated values

Preliminary

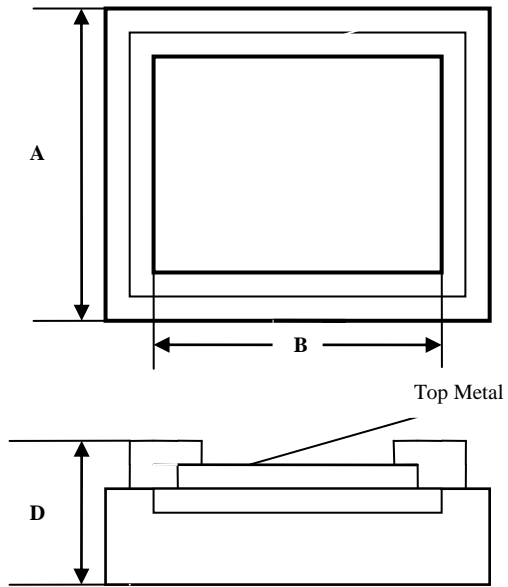
Parameter	Symbol	Unit	min	max
Repetitive peak reverse voltage	$V_{RRM}$	V	-	1800
Continuous forward current	$I_F$	A	-	100
Repetitive peak forward current*	$I_{FRM}$	A	-	200
Junction temperature	$T_{vj}$	°C	-	150

\*Limited by  $T_{vj\ max}$ **Diode Characteristics values**

Parameter	Symbol	Conditions	min	typ	max	Unit
Continuous forward voltage	$V_F$	$I_F=100A, T_{vj}= 25^\circ C$		2.4		V
Continuous reverse current	$I_R$	$V_R=1800V \begin{matrix} T_{vj}= 25^\circ C \\ T_{vj}= 125^\circ C \end{matrix}$			100	uA mA
Peak reverse recovery current	$I_{RRM}$	$I_F=100A, V_R=700V,$ $di_F/dt=200A/uS,$ $T_{vj}= 25^\circ C$		tbd		A
Recovered charge	$Q_{rr}$			tbd		$\mu C$
Reverse Recovery Time	$t_{rr}$			tbd		nS
Reverse Recovery Time	$t_{rr}$	$I_F=1A, V_R=30V,$ $di_F/dt=200A/uS.$		100	120	nS

**Mechanical properties***Top metal: **Al-Ti** – for Wire Bonding.**Backside metal: **Ti-Ni-Ag** – for Soldering.*

DIM	ITEM	$\mu m$
$A_x$ $A_y$	Die Size	10800 8300
D	Thickness	460max.
Scribe line Width		60



[www.vsp-mikron.com](http://www.vsp-mikron.com)